

SMD Multilayer Ceramic Capacitors

C C(CT) 41 Multilayer Ceramic Capacitor



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TANCAP TECHNOLOGY CO., LTD.

Product Name

CC41 (CT41) Multilayer Ceramic Capacitors

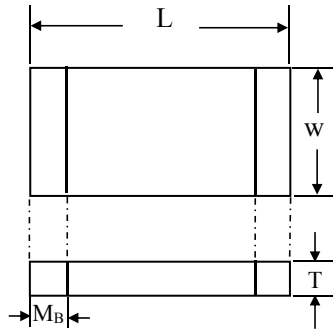


Table of working voltage Dimensions and Capacitance

Specification Of Dimension	Unit: (mm)				Working Voltage (V)	Capacitance; (pF)		
	L	W	T	M _B		NPO (COG)	X7R	Y5V (Z5U)
0402	1.00±0.05	0.50±0.05	0.50±0.05	0.2±0.15/ 0.1	16 25 50	0R5 ~ 332 0R5 ~ 222 0R5 ~ 102	331 ~ 106 331 ~ 105 331 ~ 223	103 ~ 106 103 ~ 105 103 ~ 224
0603	1.60±0.10	0.80±0.10	0.5±0.05 0.8±0.10	0.3±0.20	16 25 50	0R5 ~ 332 0R5 ~ 222 0R5 ~ 102	331 ~ 106 331 ~ 105 331 ~ 224	103 ~ 106 103 ~ 105 103 ~ 224
0805	2.00±0.20	1.25±0.20	0.7±0.2 1.0±0.2 1.25±0.2	0.5±0.20	25 50 100	0R5 ~ 332 0R5 ~ 222 0R5 ~ 102	331 ~ 106 331 ~ 105 331 ~ 223	103 ~ 106 103 ~ 105 103 ~ 224
1206	3.20±0.30	1.60±0.20	0.7±0.2 1.0±0.2 1.25±0.2	0.5±0.20	25 50 100 450	0R5 ~ 472 0R5 ~ 392 0R5 ~ 152	102 ~ 106 102 ~ 105 102 ~ 683 102 ~ 104	103 ~ 106 103 ~ 105
1210	3.20±0.30	2.50±0.30	1.25±0.3 1.5±0.3 2.0±0.3	0.75±0.20	25 50 100	561 ~ 103 561 ~ 682 561 ~ 472	102 ~ 334 102 ~ 224 102 ~ 104	104 ~ 155 104 ~ 155 104 ~ 105
1812	4.50±0.40	3.20±0.30	≤2.5	1.00±0.25	25 50 100	102 ~ 153 102 ~ 103 102 ~ 103	103 ~ 474 103 ~ 334 103 ~ 224	154 ~ 335 154 ~ 225 104 ~ 225
2225	5.70±0.50	6.40±0.50	≤2.5	1.00±0.25	25 50 100	102 ~ 473 102 ~ 223 102 ~ 103	103 ~ 105 103 ~ 105 103 ~ 474	684 ~ 475 684 ~ 335
3035	7.60±0.50	9.00±0.50	≤3.0	1.00±0.25	25 50 100	102 ~ 104 102 ~ 473 102 ~ 333	103 ~ 225 103 ~ 225 103 ~ 105	105 ~ 106 105 ~ 685

How To Order

Product description:

CT41	0805	B	104	K	250	T
Type	Size Code(mm) L*W	Dielectric	Capacitance(PF)	Tolerance	Rated Voltage	Packaging
CC41: Class I Dielectric for chip	0402 0603 0805 1206	CG=COG N=NPO A=X5R B=X7R/X7S	104= $10 \times 10^{4(\text{pf})}$ This is expressed in Pico farads. The first two digits are the significant figures. The third is the number of zeros to follow.	B=+/-0.1PF C=+/-0.25PF D=+/-0.5PF F=+/-1% G=+/-2% J=+/-5% K=+/-10% M=+/-20%	006=6.3V 100=10V 160=16V 250=25V 500=50V 630=63V 101=100V 102=1000V	T: Tape&Reel
CT41: Class II Dielectric for chip	1210 1812 2225 3035	Z=Z5U Y=Y5V				

Product Name	CC41 (CT41) Multilayer Ceramic Capacitors			
Moisture Resistance	CC41	N	No mechanical damage shall occur $\Delta C/C \leq 2\%$ $DF \leq 0.3\%$ $R \times C > 25S$	Moisture Resistance: $T=40 \pm 2^\circ C$ $t=21d$ Relative humidity: $93 \begin{smallmatrix} +2 \\ -3 \end{smallmatrix} \%$
	CT41	B	No mechanical damage shall occur $\Delta C/C \leq 10\%$ $DF \leq 5\%$ $R \times C > 25S$	Moisture Resistance: $T=40 \pm 2^\circ C$ $t=21d$ Relative humidity: $93 \begin{smallmatrix} +2 \\ -3 \end{smallmatrix} \%$
		Y	No mechanical damage shall occur $\Delta C/C \leq 20\%$ $DF \leq 7\%$ $R \times C > 25S$	Moisture Resistance: $T=40 \pm 2^\circ C$ $t=21d$ Relative humidity: $93 \begin{smallmatrix} +2 \\ -3 \end{smallmatrix} \%$
Termination adhesion strength	No mechanical damage shall occur			Test condition: 5N: $10 \pm 1S$
Vibration Test	No mechanical damage shall occur			The capacitor shall be subjected to a harmonic motion having total amplitude of 1.5mm. The entire frequency range, from 10 to 50Hz and return to 10Hz, shall be traversed in 1 minute. This cycle shall be performed 2 hours in each there mutually perpendicular direction, for total period of 6 hours.
Bending Strength	No mechanical damage shall occur, Change of capacitance Within 10%			Fix the capacitor on the PCB, Bending shall be applied to the limit (1mm) with 0.3mm/sec.
High Temperature Resistance	CC41	N	No mechanical damage shall occur $\Delta C/C \leq 2\%$ $DF \leq 0.3\%$ $R \times C > 25S$	Temperature: $+125^\circ C$ Time: 1000h Voltage: $1.5V_r$
	CT41	B	No mechanical damage shall occur $\Delta C/C \leq \pm 12.5\%$ $DF \leq 5\%$ $R \times C > 25S$	Temperature: $+125^\circ C$ Time: 1000h Voltage: $1.5V_r$
		Y	No mechanical damage shall occur $\Delta C/C \leq \pm 30\%$ $DF \leq 7\%$ $R \times C > 25S$	Temperature: $+85^\circ C$ Time: 1000h Voltage: $1.5V_r$

1. Scope:

This specification applies to CC41 (CT41) Multilayer Ceramic capacitors produced by our company for use in electronic equipment.

2. Standard:

《Detail specification for electronic components fixed ceramic dielectric capacitors CC41 Assessment level E》 SJ/T10569-94

《Detail specification for electronic components fixed ceramic dielectric capacitors CT41 Assessment level E》 SJ/T10570-94

3. Classify:

CC41: Class I dielectric, such as NPO (N), COG, electrical character is stability and not change with the temperature time and voltage basically, suit for high frequency circuit that must be high stability.

CT41: Class II dielectric, such as X7R (B) X5R(A), electrical character is stability and not change with the temperature time and voltage rapidly, suit for Blocking 、 Coupling 、 By-passing and other circuits that the requirement to stability of capacitance is not strict.

Class III dielectric, such as Y5V(Y), Z5U (Z), having high dielectric constant, it can be used to produce capacitors with more larger capacitance. But the stability of capacitance is poorer than X7R, the capacitance and $\tan\delta$ is sensitive with the temperature and voltage.

4. Test Conditions:

4.1: Standard Condition: If there are no specific prescribe, the test will be done according to standard condition (Temperature 15-35°C; Relative Humidity 45-75%); But if there are any problems subject to standard condition or there are some specific requirements, please test according to 4.2.

4.2: Fundamental Condition: Temperature is 20°C; Relative Humidity is 60-70%; Atmospheric pressure is 800-1060mbar.

5. Testing Method:

When the products will be tested, in order to avoid the error of result, the capacitors must be placed in the temperature that the capacitors be tested for 30 minutes and discharged fully.

6. Test Items:

Product Name		CC41 (CT41) Multilayer Ceramic Capacitors				
Dimensions	See page 4			Measured by dimension gauge		
Insulation Resistance	CC41	$C_R \leq 10nF$ $R \geq 10000M\Omega$ $C_R > 10nF$ $C_R \times R \geq 100s$		Rated voltage applied for 1minute Charging current $\leq 50mA$		
	CT41	$C_R \leq 25nF$ $R \geq 4000M\Omega$ $C_R > 25nF$ $C_R \times R \geq 100s$				
Capacitance Tolerance	CC41	N	J=±5% K=±10%		1MHz 1VDC	
	CT41	B	K=±10% M=±20%		1KHz 1VDC	
		Y	M=±20% S= $\begin{matrix} +50\% \\ -20\% \end{matrix}$ Z= $\begin{matrix} +80\% \\ -20\% \end{matrix}$		1KHz 0.3VDC	
Dissipation Factor (Tanδ)	CC41	N	DF≤0.15%		1MHz 1VDC	
	CT41	B	DF≤2.5%		1KHz 1VDC	
		Y	$C_R < 1\mu F$	DF≤5%		1KHz 0.3VDC
			$C_R \geq 1\mu F$	DF≤7%		
Withstanding Voltage	No dielectric breakdown or mechanical breakdown			250% of the rated voltage for 1-5sec is applied with less than 50mA current		
Solderability	The dipped portion of termination is at least 95% covered by a new solder coating			Solder temperature: 235±5°C Immersion times: 2±0.5s		
Temperature Characteristics	CC41	N	$\Delta C/C$: 0±30ppm/°C		-55°C ~ +125°C	
	CT41	B	$\Delta C/C$: ±15%		-55°C ~ +125°C	
		Y	$\Delta C/C$: +30% ~ -80%		-25°C ~ +85°C	
		Z	$\Delta C/C$: +22% ~ -56%		+10°C ~ +85°C	
Temperature Cycle	CC41	N	No mechanical damage shall occur, $\Delta C/C \leq 1\%$		Low limit temperature: -55±3°C High limit temperature: +125±3°C Capacitors shall be subjected to five cycle of the temperature cycle, each for 30//	
	CT41	B	No mechanical damage shall occur, $\Delta C/C \leq \pm 10\%$		Low limit temperature: -55±3°C High limit temperature: +125±3°C Capacitors shall be subjected to five cycle of the temperature cycle, each for 30//	
		Y (Z)	No mechanical damage shall occur, $\Delta C/C \leq \pm 30\%$		Low limit temperature: Y: -25±3°C, Z: +10±3°C High limit temperature: +85±3°C Capacitors shall be subjected to five cycle of the temperature cycle, each for 30//	

Application Notes for Multilayer Capacitors

1. Effect of Temperature

Both capacitance and dissipation are affected by variations in temperature. The maximum capacitance change with temperature is defined by the temperature characteristic. However, this only defines a “box” bounded by the upper and lower operating temperatures and the minimum and maximum capacitance values. Within this “box”, the variation with temperature depended upon the specific dielectric formulation.

Insulation resistance decreases with temperature. Typical the insulation resistance at maximum rated temperature is 10% of the 25°C value.

2. Effect of Voltage

Class I ceramic capacitors are not affected by variations in applied AC or DC voltages. For Class II and III ceramic capacitors, variations in voltage affect only the capacitance and dissipation factor. The application of DC voltage higher than 5 DC reduces both the capacitance and dissipation factor. The application of AC voltage up to 10-20 Vac tend to increase both capacitance and dissipation factor. At higher AC voltage, both capacitance and dissipation factor begin to decrease.

3. Effect of Frequency

Frequency affects both capacitance and dissipation factor.

The variation of impedance with frequency is an important consideration in the application of multilayer ceramic capacitors. Total impedance of the capacitor is the vector of the capacitive reactance, the inductive reactance, and the ESR. As frequency increases, the capacitive reactance decreases. However, the series inductance (L) produces inductive reactance, which increases with frequency. At some frequency, the impedance ceases to be capacitive and becomes inductive. This point is the self-resonant frequency. At the self-resonant frequency, the reactance is zero, and the impedance consists of the ESR only.

Lead configuration and lead length have a significant impact on the series inductance. The lead inductance is approximately 10nH/inch, which is large compared to the inductance of chip. The effect of this additional inductance is a decrease in the self-resonant frequency, and an increase in impedance in the inductive region above the self- resonant frequency.

4. Effect of Time

The capacitance of Class II and III dielectrics change with time as well as with temperature, voltage and frequency. This change with time is known as “aging”. It is caused by gradual realignment of the crystalline structure of the ceramic dielectric material as it is cooled below its Curie temperature, which produces a loss of capacitance with time. The aging process is predictable and follows a logarithmic decay. Typical aging rates for COG, X7R, and Z5U dielectrics are as follows:

COG:	None
X7R:	1.0% per decade of time
Z5U:	5.0% per decade of time
Y5V:	6.0% per decade of time

The aging process is reversible. If the capacitor is heated to a temperature above its Curie point for some period of time, de-aging will occur and the capacitor will regain the capacitance lost during the aging process. The amount of de-aging depends on both the elevated temperature and the length of time at that temperature. Exposure to 150°C for one-half hour or 125°C for two hours is usually sufficient to return the capacitor to its initial value.

Because the capacitance changes rapidly immediately after de-aging, capacitance measurements are usually delayed for at least 10 hours after the de-aging process, which is often referred to as "last heat". In addition, manufacturers utilize the aging rates to set factory test limits which will bring the capacitance within the specified tolerance at some future time, to allow for customer receipt and use. Typically, the test limits are adjusted so that capacitance will be within the specified tolerance after either 1,000 hours or 100 days, depending on the manufacturer and the product type.

5. Thermal Shock

Multilayer ceramic capacitors are sensitive to thermal shock due to device construction consisting of interleaved layers of ceramic dielectric and metal electrodes with metal terminations for electrical contact. Thermal shock is mechanical damage caused by a structure's inability to absorb mechanical stress caused by excessive changes of temperature in a short period of time. This stress is caused by differences in CTE (coefficient of thermal expansion), δT (thermal conductivity) and the rate of change of temperature. CTE and δT are a function of the materials used in the component's manufacture and the rate of change of temperature is dependent on the soldering process. When the temperature rate of change is too great, thermal shock cracks occur. These cracks are initiated where the structure is weakest and mechanical stress is concentrated. This is at or near the ceramic / termination interface in the middle of the exposed termination. Mechanical stress is greatest at the corners where the chip is strongest but cracks tend to start where the structure is weakest. When temperature rates of change are excessive, as in uncontrolled wave soldering, large visible cracks are formed.

Thermal shock has two manifestations: obvious visible cracks and the more insidious, invisible micro crack. The same forces are involved but on a smaller magnitude so smaller cracks are formed. Again it starts in the middle of the exposed surface at or just under the ceramic / termination interface and propagates slowly with temperature changes or assembly flexure during handling. In a matter of weeks a micro crack can propagate through the ceramic causing open, intermittent or excessive leakage currents, a time bomb due to processing.

Thermal shock cracks are always caused by improper solder processing or clearing. Wave soldering is the biggest culprit because it has the highest heat transfer rate (using liquid metal) and the largest temperature changes which cause both visible and micro cracks. Vapor phase soldering has the second highest heat transfer rate and temperature changes that can induce micro cracks when inadequate preheat is used. Infrared (IR) reflow soldering has the lowest heat transfer rates and thermal shock is unheard of for this soldering technique. Assembly cleaning cannot be ignored because thermal shock can occur during heating or cooling. An assembly should be allowed to cool to less than 60°C before it is subjected to the cleaning process.

It is important to avoid the possibility of thermal shock during soldering and carefully controlled preheat is therefore required. The rate of preheat should not exceed 4°C/second and a target figure 2°C/second is recommended. An 80°C to 120°C temperature differential between the component surface and the soldering temperature is preferred.